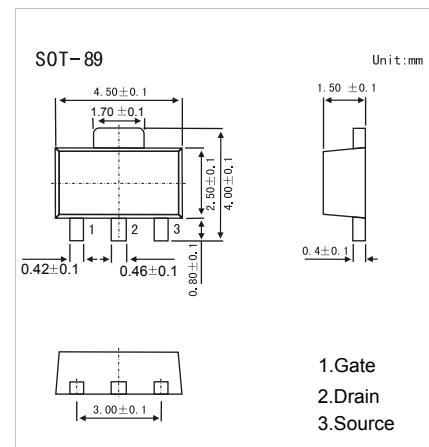
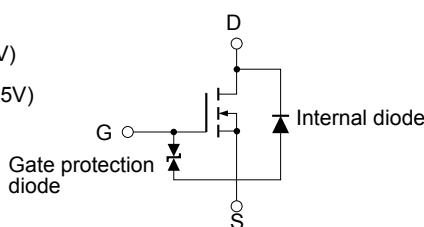


N-Channel MOSFET

2SK2159

■ Features

- $V_{DS}(V) = 60V$
- $I_D = 2 A$
- $R_{DS(ON)} < 0.3 \Omega$ ($V_{GS} = 4V$)
- $R_{DS(ON)} < 0.5 \Omega$ ($V_{GS} = 2.5V$)

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 14	
Continuous Drain Current	I_D	2	A
Pulsed Drain Current (Note.1)	I_{DM}	4	
Power Dissipation	P_D	2	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{STG}	-55 to 150	

Note.1: $PW \leq 10ms$, Duty Cycle $\leq 50\%$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	$I_D=250 \mu A$, $V_{GS}=0V$	60			V
Zero Gate Voltage Drain Current	$I_{DS(on)}$	$V_{DS}=60 V$, $V_{GS}=0V$			1	μA
Gate-Body Leakage Current	$I_{GS(on)}$	$V_{DS}=0V$, $V_{GS}=\pm 14V$			± 10	μA
Gate Cut-off Voltage	$V_{GS(off)}$	$V_{DS}=10V$, $I_D=1mA$	0.5		1.1	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4V$, $I_D=1A$			0.3	Ω
		$V_{GS}=2.5V$, $I_D=1A$			0.5	
		$V_{GS}=1.5V$, $I_D=0.1A$			0.7	
Forward Transconductance	g_{FS}	$V_{DS}=10V$, $I_D=1A$	0.4			S
Input Capacitance	C_{iss}	$V_{GS}=0V$, $V_{DS}=10V$, $f=1MHz$		319		pF
Output Capacitance	C_{oss}			109		
Reverse Transfer Capacitance	C_{rss}			22		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS(on)}=3V$, $V_{DS}=25V$, $I_D=1A$, $R_L=25 \Omega$, $R_G=10 \Omega$		38		ns
Turn-On Rise Time	t_r			128		
Turn-Off Delay Time	$t_{d(off)}$			237		
Turn-Off Fall Time	t_f			130		

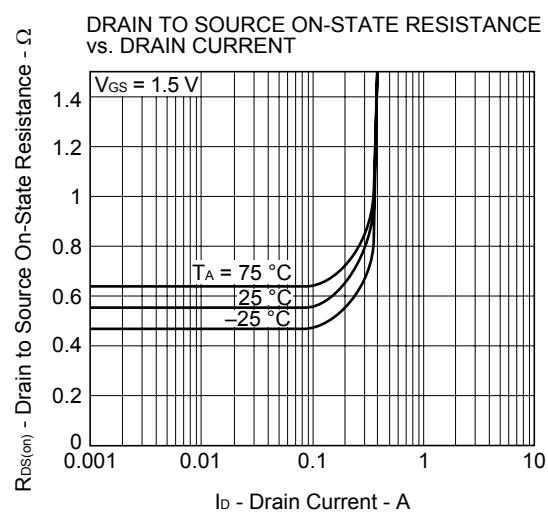
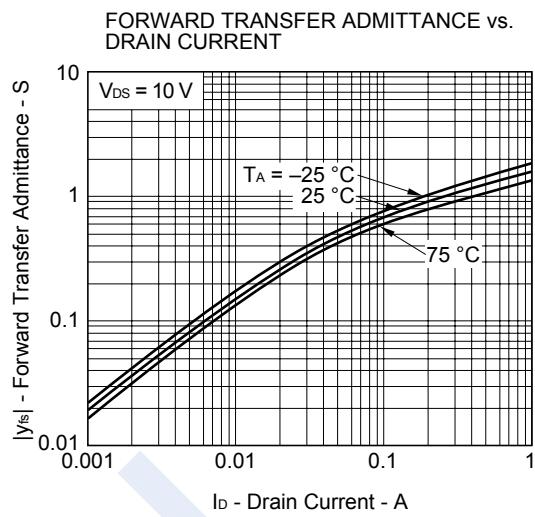
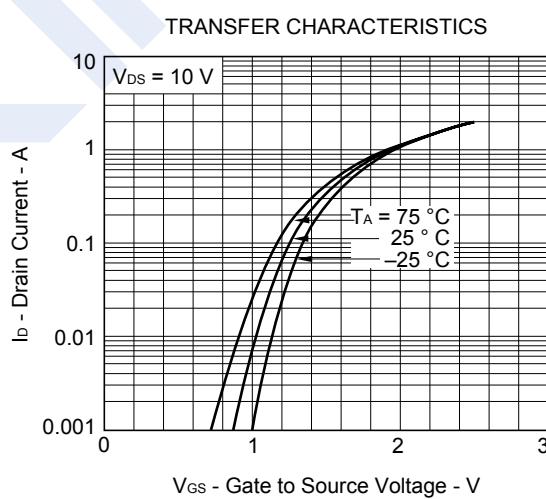
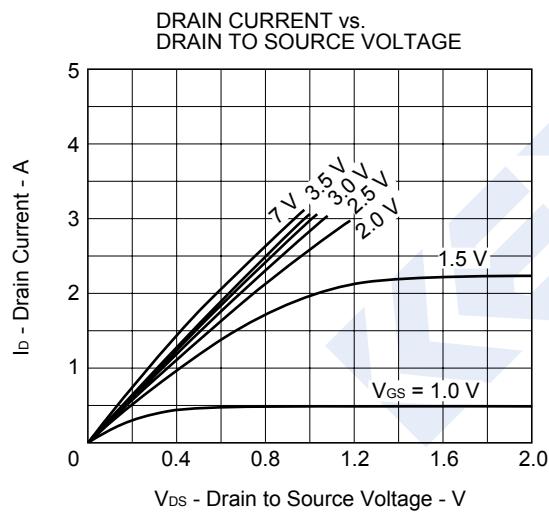
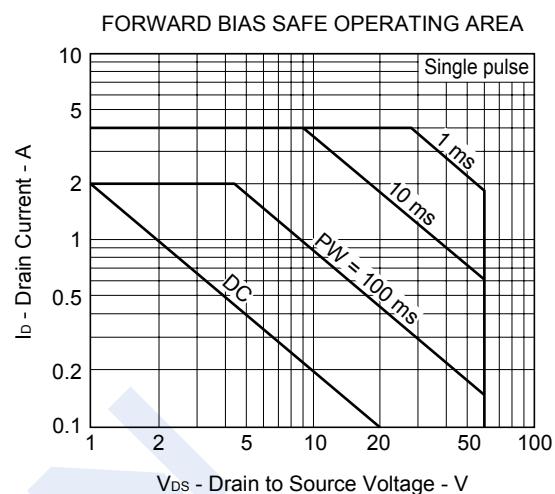
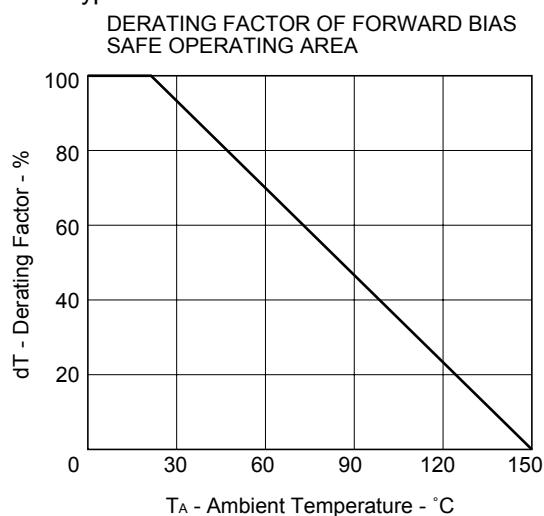
■ Marking

Marking	NW
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N-Channel MOSFET

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■ Typical Characteristics



N-Channel MOSFET

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■ Typical Characteristics

